

Silicon NPN Power Transistors

2SD425 2SD426

DESCRIPTION

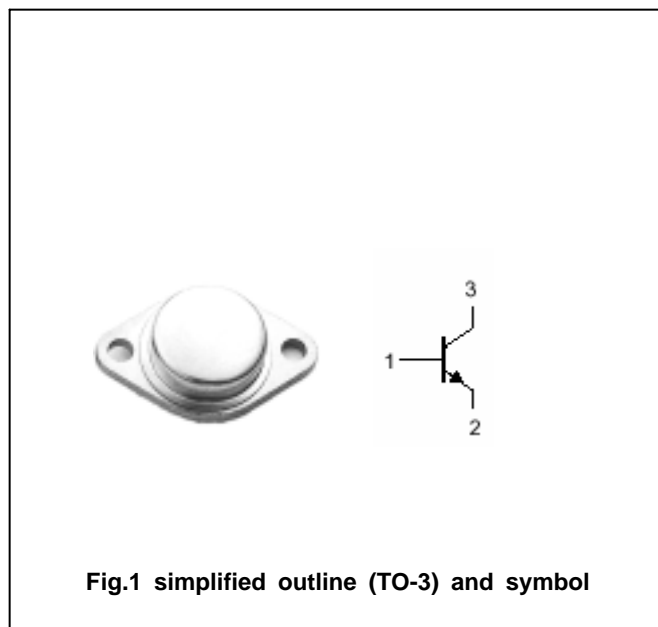
- With TO-3 package
- Complement to type 2SB555/556
- High power dissipation

APPLICATIONS

- Power amplifier applications
- Recommended for high-power high-fidelity audio frequency amplifier output stage

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SD425	140	V
		2SD426	120	
V _{CEO}	Collector-emitter voltage	2SD425	140	V
		2SD426	120	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		12	A
I _E	Emitter current		12	A
P _C	Collector power dissipation	T _C =25	100	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SD425	I _C =0.1A ; I _B =0	140			V
		2SD426		120			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =10mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	2SD425	I _C =7A ; I _B =0.7A			3.0	V
		2SD426	I _C =6A ; I _B =0.6A				
V _{BE}	Base-emitter on voltage		I _C =7A ; V _{CE} =5V			2.5	V
I _{CBO}	Collector cut-off current		V _{CB} =50V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current		V _{EB} =5V ; I _C =0			0.1	mA
h _{FE}	DC current gain		I _C =2A ; V _{CE} =5V	40		140	
f _T	Transition frequency		I _C =2A ; V _{CE} =5V		5		MHz

PACKAGE OUTLINE

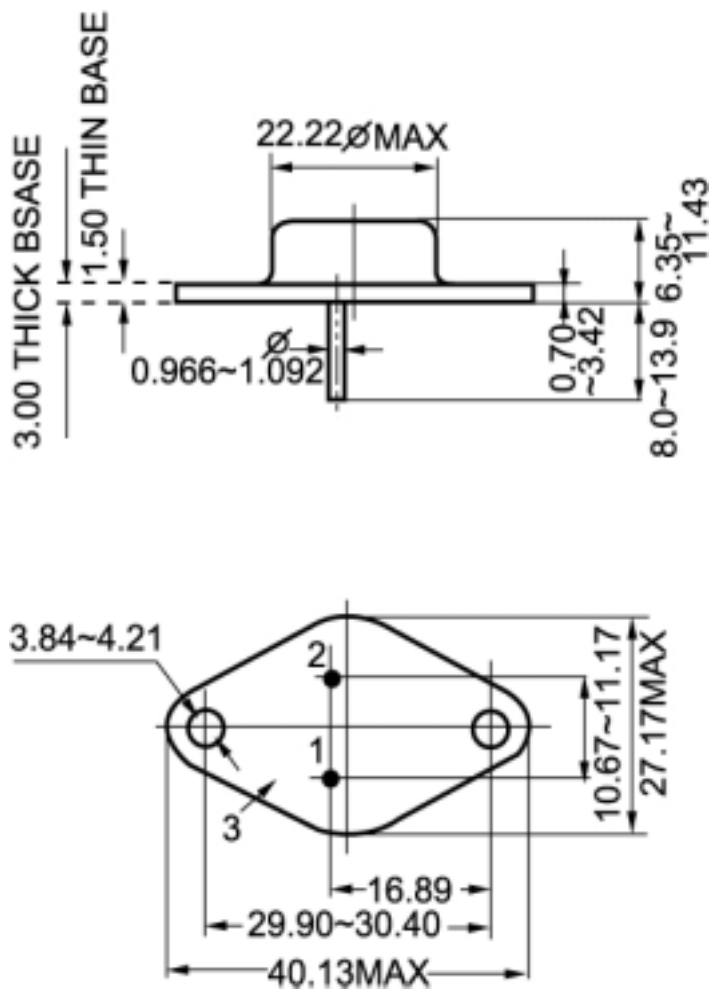


Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)